



Sheet 1 of 1

Form 1449*

Applicant: Leonard Forbes et al.

Serial No. 08/902,133

INFORMATION DISCLOSURE STATEMENT
BY APPLICANT
(Use several sheets if necessary)

Filing Date: July 29, 1997

Group: 2815

U.S. PATENT DOCUMENTS

| **Examiner Initial | Document Number | Date | Name | Class | Subclass | Filing Date If Appropriate |
|-----------------------|-----------------|------------|---------|-------|----------|-------------------------------|
| <i>Wm</i> | 5,846,859 | 12/08/1998 | Lee, S. | 438 | 253 | 02/23/96 |

FOREIGN PATENT DOCUMENTS

| **Examiner Initial | Document Number | Date | Country | Class | Subclass | Translation Yes No |
|-----------------------|-----------------|------------|---------|-------|----------|-------------------------|
| <i>Wm</i> | 60-184681 | 09/20/1985 | Japan | C23C | 16/30 | |
| <i>Wm</i> | 60-242678 | 12/02/1985 | Japan | H01L | 29/73 | |

OTHER DOCUMENTS

(Including Author, Title, Date, Pertinent Pages, Etc.)

| **Examiner Initial | |
|-----------------------|---|
| <i>Wm</i> | Beltram, F., et al., "GaAIAs/GaAs Floating-Gate Memory Devices with Graded-Gap Injector Grown by Molecular-Beam Epitaxy", <u>IEEE Transactions on Electron Devices</u> , 35, Abstract No. VA-7, 2451, (Dec. 1988) |
| <i>Wm</i> | Lin, B.J., et al., "Dramatic Reduction of Sidegating in MODFET's", <u>IEEE Transactions on Electron Devices</u> , 35, Abstract No. VA-6, 2451, (Dec. 1988) |
| <i>Wm</i> | Lott, J.A., et al., "Charge Storage in InAIAs/InGaAs/InP Floating Gate Heterostructures", <u>Electronics Letters</u> , 26, 972-973, (July 5, 1990) |
| <i>Wm</i> | Mohammad, S.N., et al., "Emerging Gallium Nitride Based Devices", <u>Proceedings of the IEEE</u> , 83, 1306-1355, (Oct. 1995) |

RECEIVED

MAY 21 1999

TECHNOLOGY CENTER 2800

Examiner

v. Mark Wallen

Date Considered

5/26/99

*Substitute Disclosure Statement Form (PTO-1449)

**EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.